Physics ICS Part 2 Chapter 18 Online MCQ's Test

Sr	Questions	Answers Choice
1	An expression for gain of an inverting amplifier is	C. (R₁R₂) D. None of these
2	One use of a single p-n junction semiconductor in an electrical circuit is a	A. Rectifier B. Transistor C. Battery D. Diode
3	Which one has greater cone of impurity among all:	A. Emitter B. Base C. Collector D. All are pure
4	Transistor was discovered by	A. Young B. Curie C. John Bardeen D. Shale's
5	Automatic function of street light can be done by the use of.	A. Inductor B. Rectifier C. Comparator D. emf
6	Which diode works at reverse biasing.	A. LED B. Photo voltaic cell C. Photo diode D. Silicon diode
7	The circuit of full wave rectification consist of	A. Three diodes B. Four diodes C. Two diodes D. One diode
8	A light emitting diode emits light only when	A. Reverse biased B. Forward biased C. Unbiased D. None of these
9	The resistance between the inverting (-) and non inverting inputs is called Input resistance and is the order of.	A. Ohms B. Kilo Ohms C. Mega Ohms D. Thounds Ohms
10	Which is not fundamental logic gate.	A. NOT B. AND C. OR D. NAND
11	X=A+B is the mathematical notation for.	A. OR gate B. NOR gate C. NAND gate D. AND gate
12	For normal use:	A. Emitter base function is reversed biased B. Collector base junction is reserved biased C. Emitter base junction is forward biased D. Both c and b
13	the number of terminals in a semiconductor diode are	A. 2 B. 3 C. 4 D. 5
14	During negative half cycle of A.c then p-n junction offers.	A. High resistance B. Low resistance C. No resistance D. All of these
15	A two inputs NAND gat with inputs a and b has an output '0' if.	A. B is zero B. A is zero C. Both A and B are 1

		D. Both A and B are '0'
16	The p-n junction in which p side is connected to+ive and n-side is -ve the junction is said to be:	A. Neutral B. Forward biased C. Reversed biased D. None of above
17	The P.D develop in case of silicon is:	A. 0.7V B. 0.3V C. 0.5V D. 0.9V
18	Light emitting diodes are made from semiconductors.	A. Silicon B. Germanium C. Carbon D. Gallium arsenide
19	The average gap for Germanium at 0K is	A. 1.12 ev B. 0.02 ev C. 6.72 ev D. 7.2 ev
20	The potential difference across depletion region in case of Si is	A. 0.6 volt B. 0.9 volt C. 0.7 volt D. 0.2 volt